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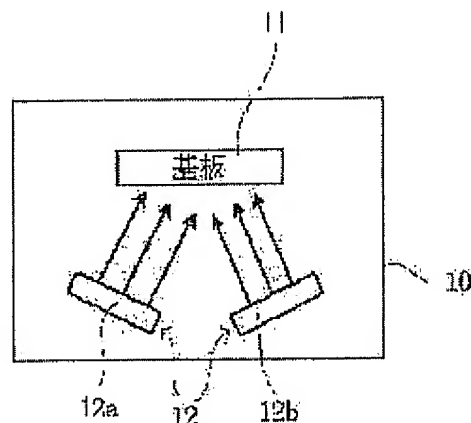
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## (54) FORMATION OF SPUTTERING FILM

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a method for forming a sputtering film by which the distribution of the film in the plane of a substrate is improved, and the excellent film thickness uniformity of the sputtering film can be attained.

SOLUTION: In a method for forming a sputtering film to a substrate in which, in a sputtering chamber 10, a substrate 11 is moved at a prescribed rate, and a sputtering film by sputtering particles from a target deposited in the sputtering chamber is formed on the surface of the substrate, a pair of targets 12a and 12b are deposited right and left along the rectangular direction to the moving direction of the substrate, furthermore, these pair of targets are arranged obliquely to respective substrate faces in a state in which the faces on the substrate sides are mutually confronted, and sputtering film formation is executed.



## LEGAL STATUS

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